

Vishay Siliconix

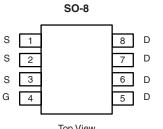
P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)				
- 30	0.042 at V _{GS} = - 10 V	- 5.7				
	0.055 at V _{GS} = - 6 V	- 5.0				
	0.070 at V _{GS} = - 4.5 V	- 4.4				

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET ٠
- Compliant to RoHS Directive 2002/95/EC •





Top View

Ordering Information: Si9435BDY-T1-E3 (Lead (Pb)-free) Si9435BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

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s

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 \ ^{\circ}C$, unless	ss otherwise n	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		V
	T _A = 25 °C	I _D	- 5.7	- 4.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.6	- 3.2	
Pulsed Drain Current		I _{DM}	- 30		А
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 2.3	- 1.1	
	T _A = 25 °C	- P _D	2.5	1.3	w
Maximum Power Dissipation ^a	T _A = 70 °C		1.6	0.8	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	- R _{thJA}	40	50	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		70	95		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	24	30		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
	I _{DSS}	$V_{DS} = -30 V, V_{GS} = 0 V$			- 1		
Zero Gate Voltage Drain Current		V_{DS} = - 30 V, V_{GS} = 0 V, T_{J} = 70 °C			- 5	μA	
	I	$V_{DS}{\leq}$ - 10 V, $V_{GS}{=}$ - 10 V	- 20			•	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 5			A	
		V _{GS} = - 10 V, I _D = - 5.7 A		0.033	0.042	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = - 6 V, I _D = - 5 A		0.043	0.055		
		V _{GS} = - 4.5 V, I _D = - 4.4 A		0.056	0.070		
Forward Transconductance ^b	9 _{fs}	V _{DS} = - 15 V, I _D = - 5.7 A		13		S	
Diode Forward Voltage ^b	V_{SD}	$I_{S} = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.1	V	
Dynamic ^a				•			
Total Gate Charge	Qg			16	24		
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 10 V, I_{D} = - 3.5 A		2.3		nC	
Gate-Drain Charge	Q _{gd}			4.5			
Gate Resistance	R _g			8.8		Ω	
Turn-On Delay Time	t _{d(on)}			14	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	25		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 10 V, R_g = 6 Ω		42	70	ns	
Fall Time	t _f			30	50		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.2 A, dl/dt = 100 A/μs		30	60		

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

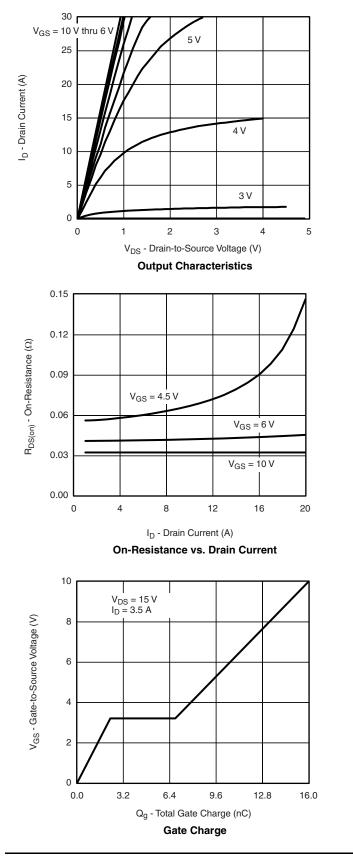
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

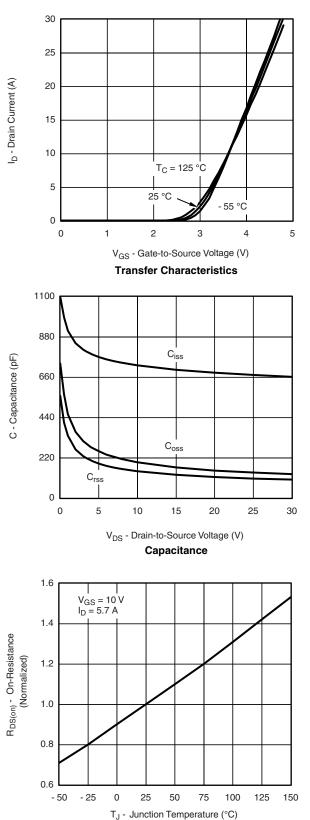


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





On-Resistance vs. Junction Temperature

Si9435BDY

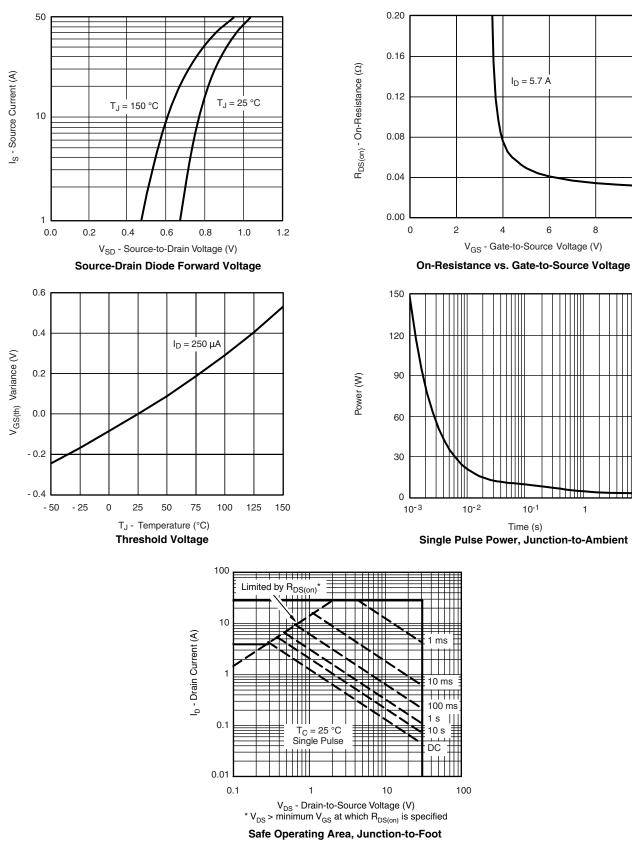
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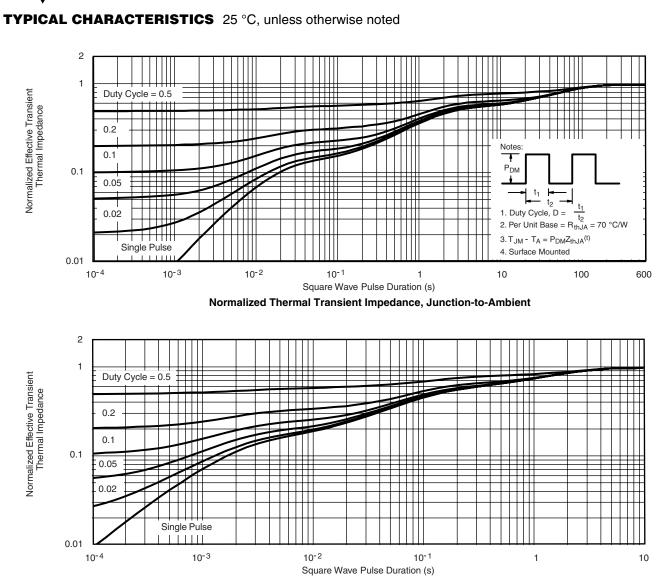
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg772245.

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Si9435BDY

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Package Information

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INCHES			
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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